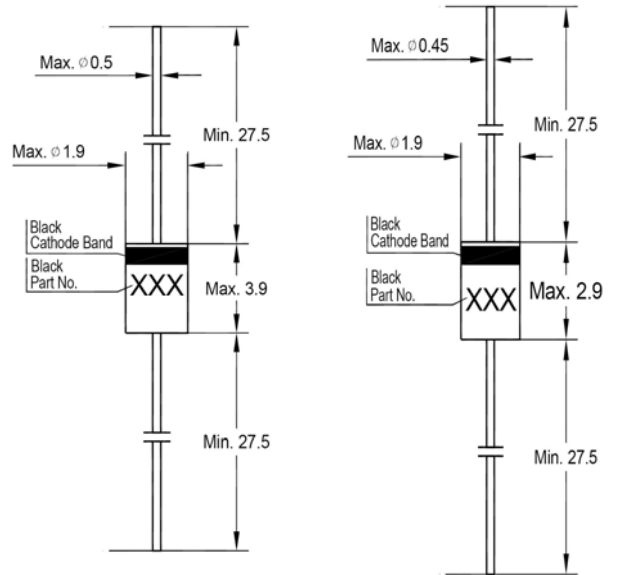


# 1N4148

## Silicon Epitaxial Planar Switching Diode

### FEATURES

- ◆ High-speed switching
- ◆ This diode is also available in MiniMELF case  
With the type designation LL4148



Glass Case DO-35  
Dimensions in mm

Glass Case DO-34  
Dimensions in mm

### Absolute Maximum Ratings (Ta = 25°C)

PARAMETER	SYMBOL	VALUE	UNIT
Peak Reverse Voltage	$V_{RM}$	100	V
Reverse Voltage	$V_R$	75	V
Average Rectified Forward Current	$I_{F(AV)}$	200	mA
Non-repetitive Peak Forward Surge Current	$I_{FSM}$	0.5	A
at t = 1 s		1	
at t = 1 ms		4	
at t = 1 $\mu$ s			
Power Dissipation	$P_{tot}$	500 <sup>1)</sup>	mW
Junction Temperature	$T_j$	200	°C
Storage Temperature Range	$T_{stg}$	- 65 to + 200	°C

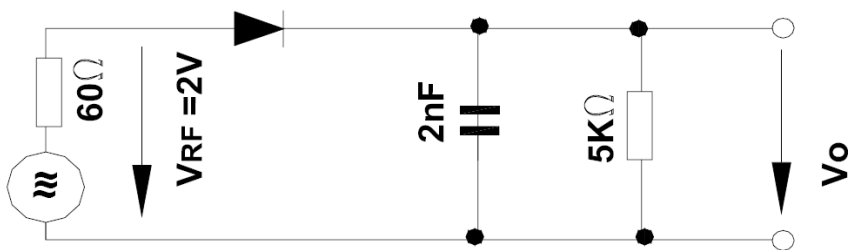
<sup>1)</sup> Valid provided that leads at a distance of 8 mm from case are kept at ambient temperature.

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## Characteristics at Ta = 25°C

PARAMETER	SYMBOL	MIN.	MAX.	UNIT
Forward Voltage at I <sub>F</sub> = 10 mA	V <sub>F</sub>	-	1	V
Leakage Current				
at V <sub>R</sub> = 20 V	I <sub>R</sub>	-	25	nA
at V <sub>R</sub> = 75 V	I <sub>R</sub>	-	5	μA
at V <sub>R</sub> = 20 V, T <sub>j</sub> = 150°C	I <sub>R</sub>	-	50	μA
Reverse Breakdown Voltage				
at I <sub>R</sub> = 100 μA	V <sub>(BR)R</sub>	100	-	V
at I <sub>R</sub> = 5 μA	V <sub>(BR)R</sub>	75	-	V
Capacitance				
at V <sub>R</sub> = 0, f = 1 MHz	C <sub>tot</sub>	-	4	pF
Voltage Rise when Switching ON				
tested with 50 mA Forward Pulses	V <sub>fr</sub>	-	2.5	V
tp = 0.1 s, Rise Time < 30 ns, fp = 5 to 100 KHz				
Reverse Recovery Time				
at I <sub>F</sub> = 10 mA to I <sub>R</sub> = 1 mA, V <sub>R</sub> = 6 V, R <sub>L</sub> = 100 Ω	t <sub>rr</sub>	-	4	ns
Thermal Resistance Junction to Ambient Air	R <sub>thA</sub>	-	0.35 <sup>1)</sup>	K/mW
Rectification Efficiency at f = 100 MHz, V <sub>RF</sub> = 2 V	η <sub>v</sub>	0.45	-	-

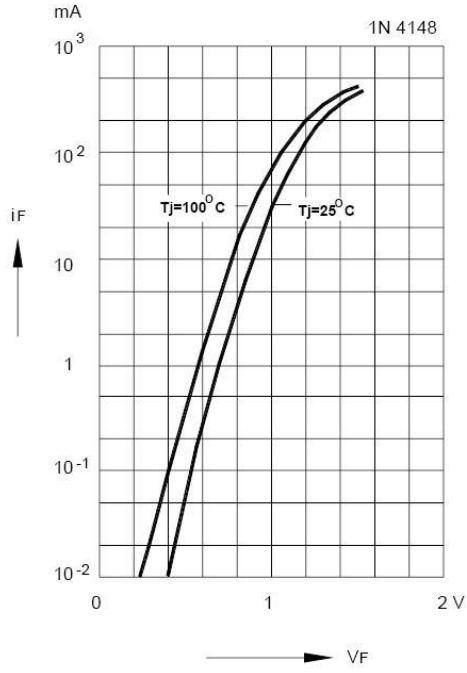
<sup>1)</sup> Valid provided that leads at a distance of 8 mm from case are kept at ambient temperature.



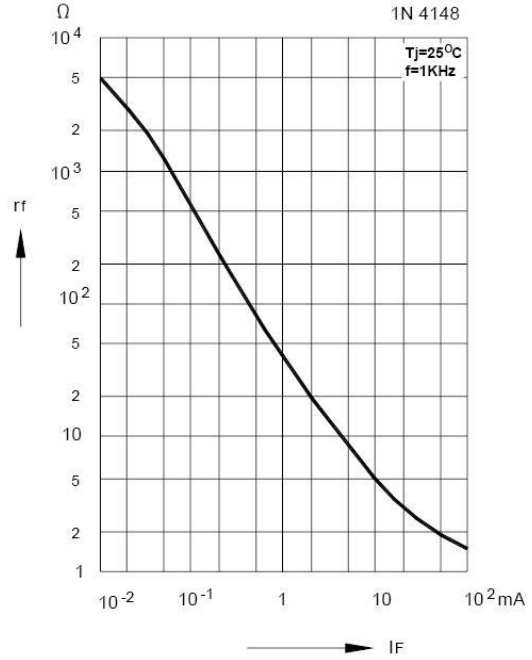
**Rectification Efficiency Measurement Circuit**

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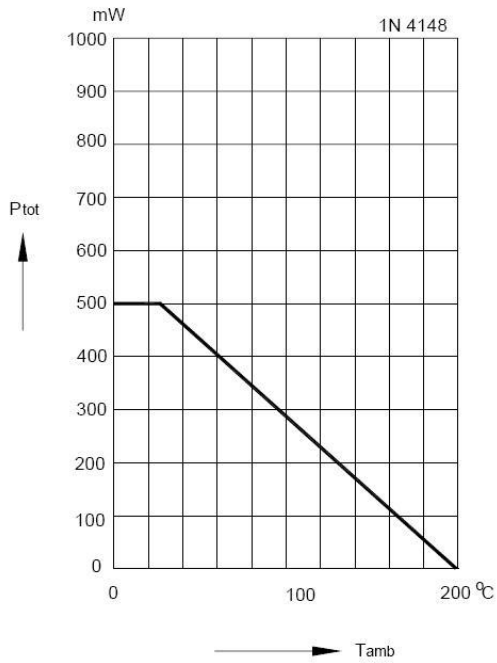
**Forward characteristics**



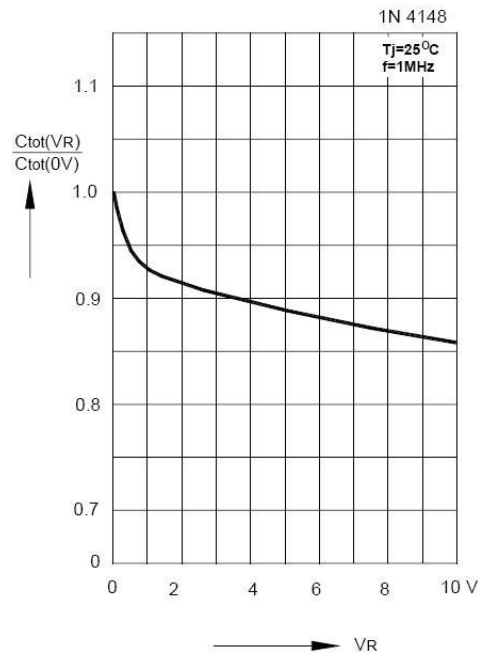
**Dynamic forward resistance versus forward current**



**Admissible power dissipation versus ambient temperature**  
Valid provided that leads at a distance of 8 mm from case are kept at ambient temperature

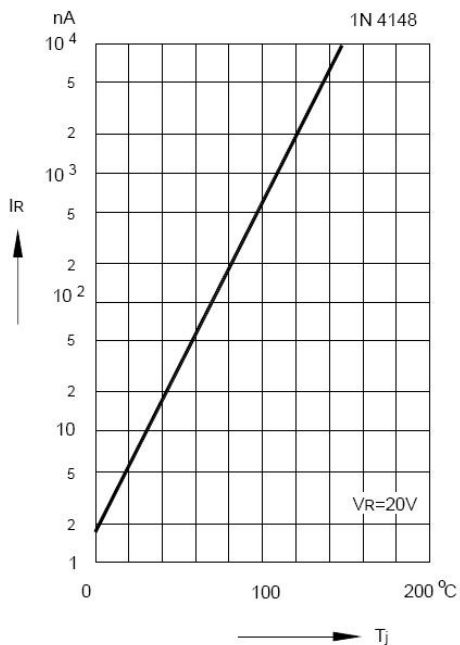


**Relative capacitance versus reverse voltage**



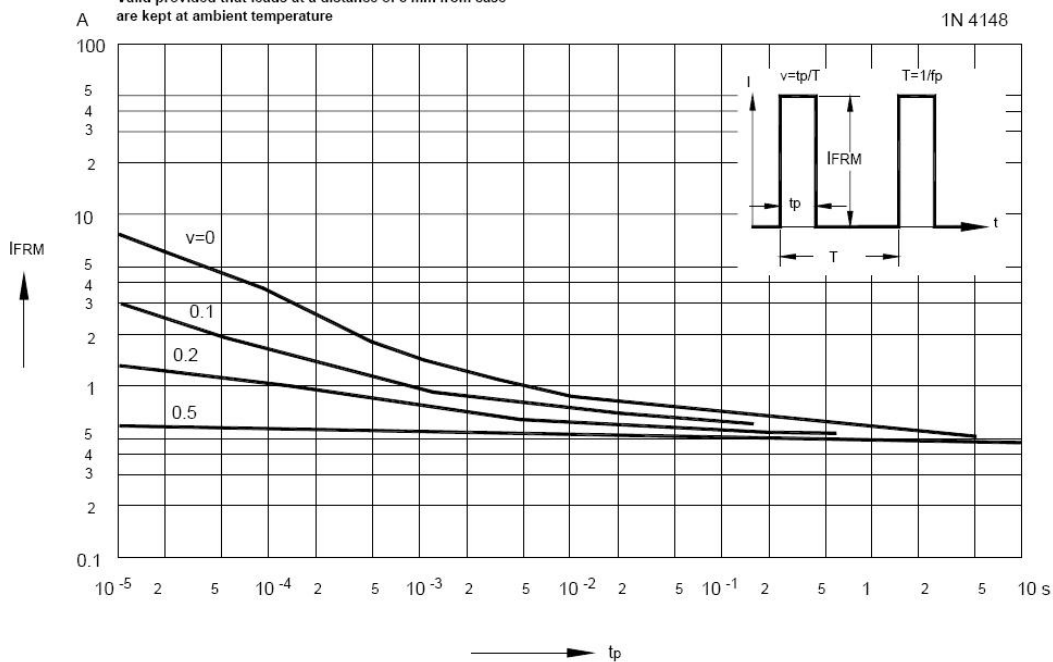
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**Leakage current versus junction temperature**



**Admissible repetitive peak forward current versus pulse duration**

Valid provided that leads at a distance of 8 mm from case are kept at ambient temperature



Note: Specifications are subject to change without notice.